



CY7C170A

4K x 4 Static RAM

Features

- CMOS for optimum speed/power
- High speed
 - $t_{AA} = 15 \text{ ns}$
 - $t_{ACS} = 10 \text{ ns}$
- Low active power
 - 495 mW (commercial)
 - 660 mW (military)
- TTL-compatible inputs and outputs
- Capable of withstanding greater than 2001V electrostatic discharge
- Output enable
- V_{IH} of 2.2V

Functional Description

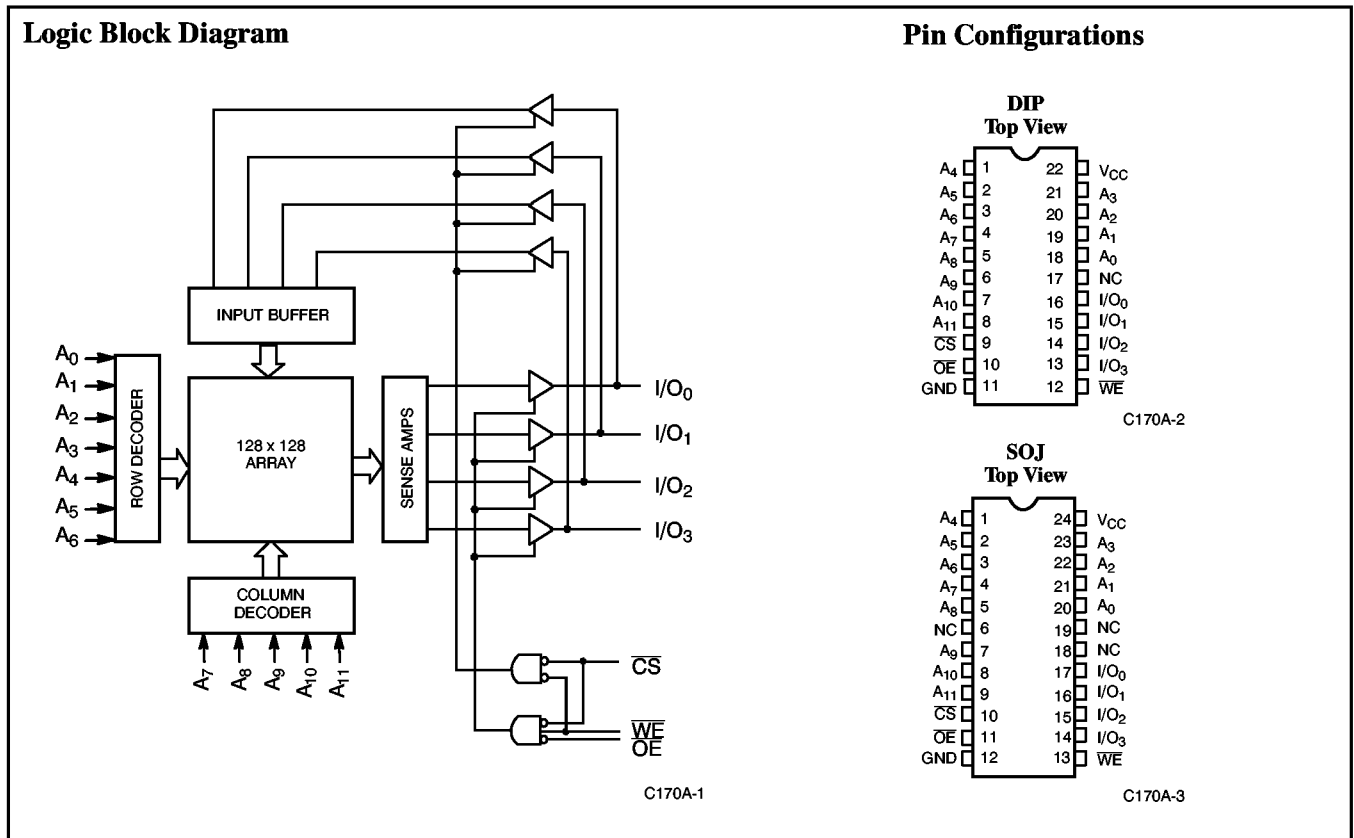
The CY7C170A is a high-performance CMOS static RAM organized as 4096 words by 4 bits. Easy memory expansion is provided by an active LOW chip select (\overline{CS}), an active LOW output enable (\overline{OE}) and three-state drivers.

Writing to the device is accomplished when the chip select (\overline{CS}) and write enable (\overline{WE}) inputs are both LOW. Data on the four input/output pins (I/O_0 through I/O_3) is written into the memory location specified on the address pins (A_0 through A_{11}).

Reading the device is accomplished by taking chip select (\overline{CS}) and output enable (\overline{OE}) LOW, while write enable (\overline{WE}) remains HIGH. Under these conditions, the contents of the memory location specified on the address pins will appear on the four data I/O pins.

The I/O pins stay in high-impedance state when chip select (\overline{CS}) or output enable (\overline{OE}) is HIGH, or write enable (\overline{WE}) is LOW.

A die coat is used to insure alpha immunity.



Selection Guide

		7C170A-15	7C170A-20	7C170A-25	7C170A-35
Maximum Access Time (ns)		15	20	25	35
Maximum Operating Current (mA)	Commercial	115	90	90	90
	Military			120	

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to $+150^{\circ}\text{C}$
 Ambient Temperature with
 Power Applied -55°C to $+125^{\circ}\text{C}$
 Supply Voltage to Ground Potential
 (Pin 22 to Pin 21) -0.5V to $+7.0\text{V}$
 DC Voltage Applied to Outputs
 in High Z State -0.5V to $+7.0\text{V}$
 DC Input Voltage -3.0V to $+7.0\text{V}$
 Output Current into Outputs (LOW) 20 mA

Static Discharge Voltage $>2001\text{V}$
 (per MIL-STD-883, Method 3015)

Latch-up Current $>200\text{ mA}$

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to $+70^{\circ}\text{C}$	$5\text{V} \pm 10\%$
Military ^[1]	-55°C to $+125^{\circ}\text{C}$	$5\text{V} \pm 10\%$

Electrical Characteristics Over the Operating Range^[2]

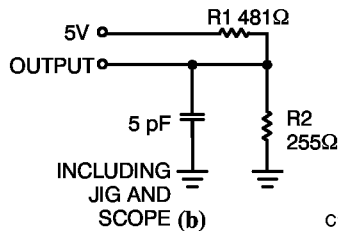
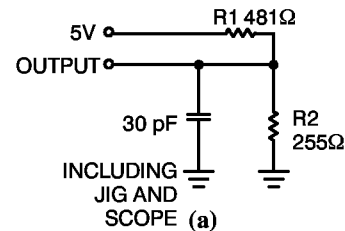
Parameter	Description	Test Conditions	7C170A-15		7C170A-20, 25, 35, 45		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -4.0 mA	2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA		0.4		0.4	V
V _{IH}	Input HIGH Voltage		2.2	V _{CC}	2.2	V _{CC}	V
V _{IL}	Input LOW Voltage		-3.0	0.8	-3.0	0.8	V
I _{IX}	Input Load Current	$\text{GND} \leq V_I \leq V_{CC}$	-10	+10	-10	+10	μA
I _{OZ}	Output Leakage Current	$\text{GND} \leq V_O \leq V_{CC}$, Output Disabled	-10	+10	-10	+10	μA
I _{OS}	Output Short Circuit Current ^[3]	V _{CC} = Max., V _{OUT} = GND		-350		-350	mA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max. I _{OUT} = 0 mA	Com ¹	115		90	mA
			Mil			120	mA

Capacitance^[4]

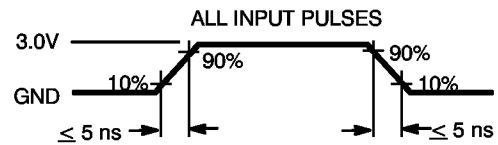
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = 5.0V	10	pF
C _{OUT}	Output Capacitance		10	pF

Notes:

1. T_A is the "instant on" case temperature.
2. See the last page of this specification for Group A subgroup testing information.
3. Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
4. Tested initially and after any design or process changes that may affect these parameters.

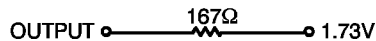
AC Test Loads and Waveforms


C170A-4



C170A-5

Equivalent to: THÉVENIN EQUIVALENT

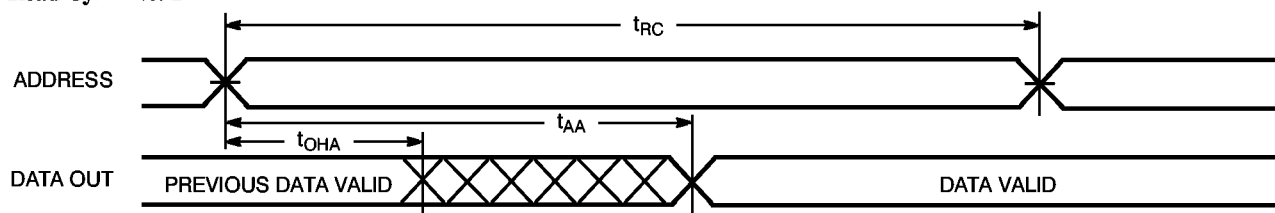


Switching Characteristics Over the Operating Range^[2, 5]

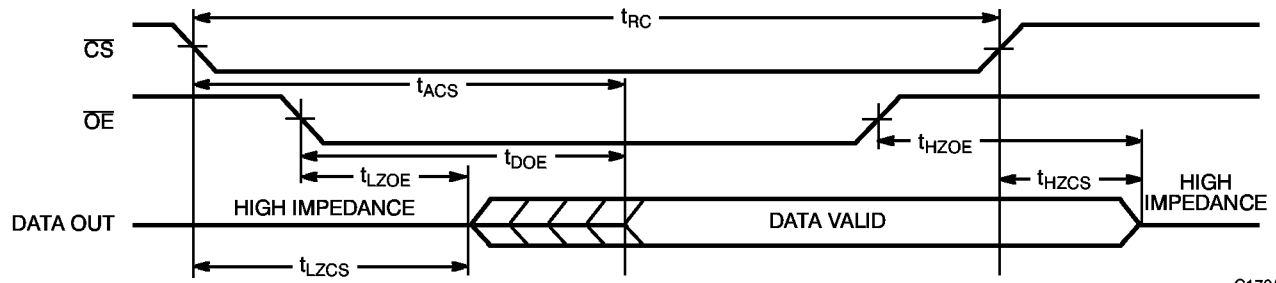
Parameter	Description	7C170A-15		7C170A-20		7C170A-25		7C170A-35		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t_{RC}	Read Cycle Time	15		20		25		35		ns
t_{AA}	Address to Data Valid		15		20		25		35	ns
t_{OHA}	Data Hold from Address Change	5		5		5		5		ns
t_{ACS}	\overline{CS} LOW to Data Valid		10		15		15		25	ns
t_{DOE}	\overline{OE} LOW to Data Valid		10		10		12		15	ns
t_{LZOE}	\overline{OE} LOW to Low Z	3		3		3		3		ns
t_{HZOE}	\overline{OE} HIGH to High Z ^[6]		8		8		10		12	ns
t_{LZCS}	\overline{CS} LOW to Low Z ^[7]	5		5		5		5		ns
t_{HZCS}	\overline{CS} HIGH to High Z ^[6, 7]		8		8		10		15	ns
WRITE CYCLE^[8]										
t_{WC}	Write Cycle Time	15		20		20		25		ns
t_{SCS}	\overline{CS} LOW to Write End	12		15		20		25		ns
t_{AW}	Address Set-Up to Write End	12		15		20		25		ns
t_{HA}	Address Hold from Write End	0		0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t_{PWE}	\overline{WE} Pulse Width	12		15		15		20		ns
t_{SD}	Data Set-Up to Write End	10		10		10		15		ns
t_{HD}	Data Hold from Write End	0		0		0		0		ns
t_{HZWE}	\overline{WE} HIGH to High Z		7		7		7		10	ns
t_{LZWE}	\overline{WE} HIGH to Low Z	5		5		5		5		ns

Notes:

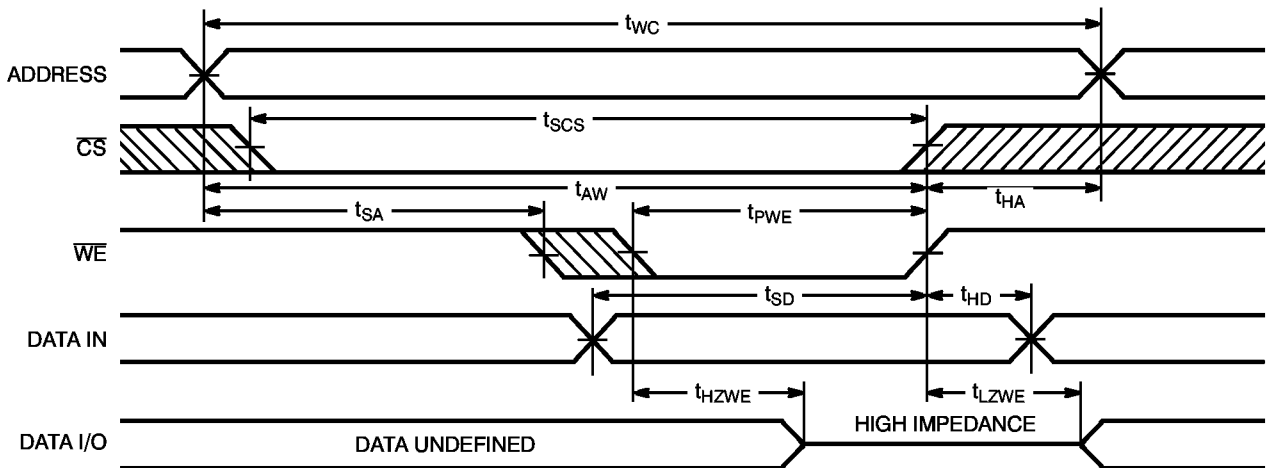
- Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading of the specified I_{OI}/I_{OH} , and 30-pF load capacitance.
- t_{HZCE} and t_{HZWE} are tested with $C_L = 5\text{pF}$ as in part (b) of AC Test Loads. Transition is measured $\pm 500\text{mV}$ from steady state voltage.
- At any given temperature and voltage condition, t_{HZCS} is less than t_{LZCS} for any given device. These parameters are sampled and not 100% tested.
- The internal write time of the memory is defined by the overlap of \overline{CS} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
- \overline{WE} is HIGH for read cycle.
- Device is continuously selected, $\overline{CS} = V_{IL}$ and $\overline{OE} = V_{IL}$.

Switching Waveforms
Read Cycle No. 1^[9, 10]


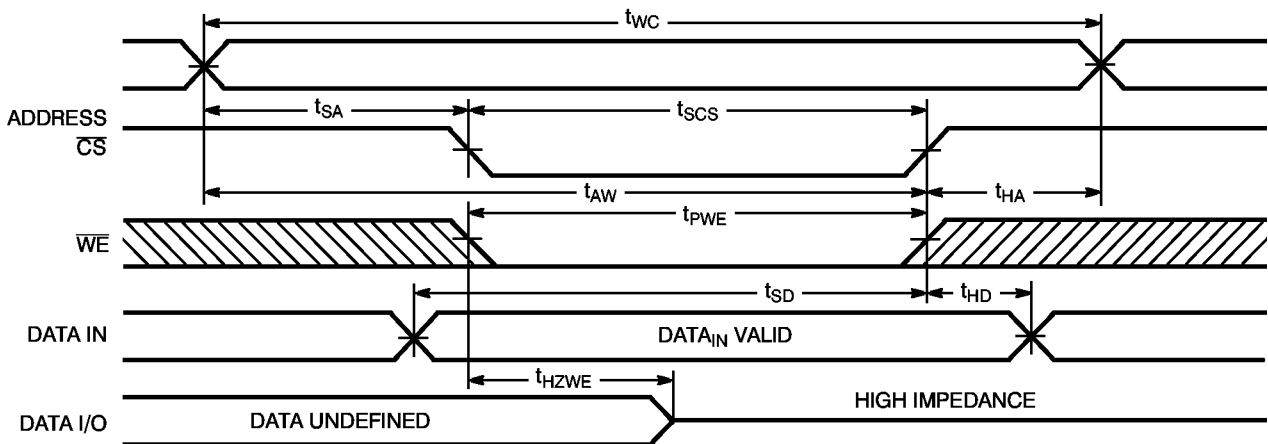
C170A-6

Switching Waveforms (continued)
Read Cycle No. 2^[9, 11]


C170A-7

Write Cycle No. 1^[8, 12]


C170A-8

Write Cycle No. 2^[8, 12, 13]


C170A-9

Notes:

 11. Data I/O will be high-impedance if $\overline{OE} = V_{IH}$.

 12. Address valid prior to or coincident with \overline{CS} transition LOW.

 13. If \overline{CS} goes HIGH simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C170A-15PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A-15VC	V13	24-Lead Molded SOJ	
20	CY7C170A-20PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A-20VC	V13	24-Lead Molded SOJ	
25	CY7C170A-25PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A-25VC	V13	24-Lead Molded SOJ	
	CY7C170A-25DMB	D10	22-Lead (300-Mil) CerDIP	Military
35	CY7C170A-35PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C170A-35VC	V13	24-Lead Molded SOJ	

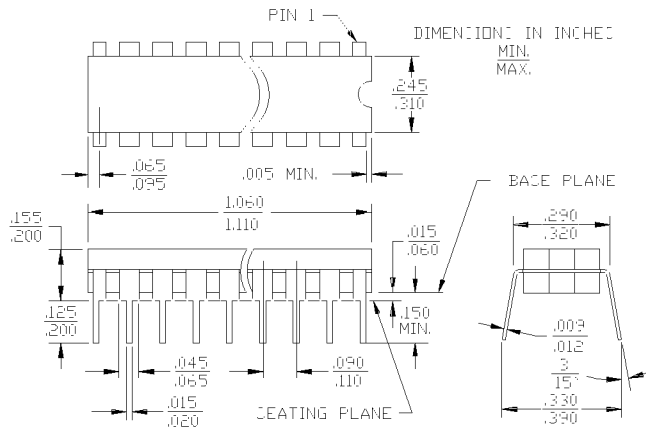
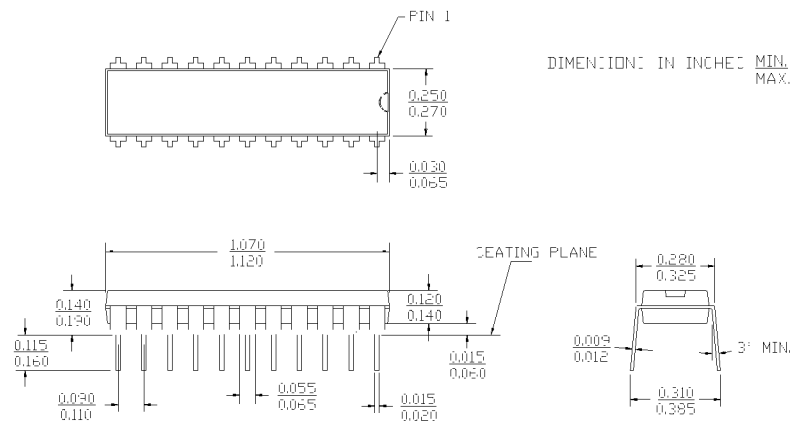
MILITARY SPECIFICATIONS
Group A Subgroup Testing
DC Characteristics

Parameter	Subgroups
V _{OH}	1, 2, 3
V _{OL}	1, 2, 3
V _{IH}	1, 2, 3
V _{IL Max.}	1, 2, 3
I _{IX}	1, 2, 3
I _{OZ}	1, 2, 3
I _{CC}	1, 2, 3

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Switching Characteristics

Parameter	Subgroups
READ CYCLE	
t _{RC}	7, 8, 9, 10, 11
t _{AA}	7, 8, 9, 10, 11
t _{OHA}	7, 8, 9, 10, 11
t _{ACS}	7, 8, 9, 10, 11
t _{DOE}	7, 8, 9, 10, 11
WRITE CYCLE	
t _{WC}	7, 8, 9, 10, 11
t _{SCS}	7, 8, 9, 10, 11
t _{AW}	7, 8, 9, 10, 11
t _{HA}	7, 8, 9, 10, 11
t _{SA}	7, 8, 9, 10, 11
t _{PWE}	7, 8, 9, 10, 11
t _{SD}	7, 8, 9, 10, 11
t _{HD}	7, 8, 9, 10, 11

Package Diagrams
22-Lead (300-Mil) CerDIP D10

22-Lead (300-Mil) Molded DIP P9


Package Diagrams (continued)
24-Lead Molded SOJ V13
